

L Number	Hits	Search Text	DB	Time stamp
1	4	6579374.pn. or 6630030.pn. or 6562140.pn. or 6572705.pn.	USPAT; US-PGPUB	2004/08/24 11:26
2	2	(ASM.as. or Lindfors.in. or Bondestam.in.) and ((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$5))) same ((control\$5 or regulat\$3 or optimiz\$5 or monitor\$3) near5 (wall or chamber or reactor) near5 temperature))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:01
3	34	(ASM.as. or Lindfors.in. or Bondestam.in.) and ((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$5))) and (substrate near5 temperature) and ((wall or reactor or chamber) near5 temperature))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 11:29
4	2	(ASM.as. or Lindfors.in. or Bondestam.in.) and ((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$5))) and ((substrate near5 temperature) with (differ\$4 or increas\$3 or decreas\$3 or higher or lower or greater or lesser) with ((wall or reactor or chamber) near5 temperature)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:06
5	12	(ASM.as. or Lindfors.in. or Bondestam.in.) and ((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$5))) with wall)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:10
6	20	(ASM.as. or Lindfors.in. or Bondestam.in.) and ((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$5))) with rate with (reduc\$5 or low\$5 or adjust\$5 or minimiz\$6 or control\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 12:33
7	3122	(427/248.1,255.23,255.28,255.7).CCLS.	USPAT; US-PGPUB	2004/08/24 12:33
8	278	(427/487).CCLS.	USPAT; US-PGPUB	2004/08/24 12:33
9	5960	(118/715,719,724,725,728).CCLS.	USPAT; US-PGPUB	2004/08/24 12:34
10	1414	(117/84,85,88,105,200,201).CCLS.	USPAT; US-PGPUB	2004/08/24 12:34
11	10149	((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)	USPAT; US-PGPUB	2004/08/24 12:34
12	11	((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$6))) near4 wall)	USPAT; US-PGPUB	2004/08/24 13:21
13	16	((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$6))) near6 wall)	USPAT; US-PGPUB	2004/08/24 13:10
14	34	((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$6))) and ((heat\$3 or temperature) near3 wall) and ((heat\$3 or temperature) near3 (support or susceptor or substrate or base or wafer)))	USPAT; US-PGPUB	2004/08/24 12:43

15	71	((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and (ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$6))) and ((deposit\$3 or decompos\$5 or condens\$5 or contaminat\$4 or coat\$3) near3 (minimiz\$5 or eliminat\$3 or prevent\$3 or avoid\$5) with (chamber or vessel or reactor or wall))	USPAT; US-PGPUB	2004/08/24 13:25
16	18	((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and (ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$5))) same ((control\$5 or regulat\$3 or optimiz\$5 or monitor\$3) near5 (wall or chamber or reactor) near5 temperature))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:02
17	17	((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and (ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$5))) same ((control\$5 or regulat\$3 or optimiz\$5 or monitor\$3) near5 (wall or chamber or reactor) near5 temperature))) not ((ASM.as. or Lindfors.in. or Bondestam.in.) and ((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$5))) same ((control\$5 or regulat\$3 or optimiz\$5 or monitor\$3) near5 (wall or chamber or reactor) near5 temperature)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:02
18	20	((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and (ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$5))) same ((control\$5 or regulat\$3 or optimiz\$5 or monitor\$3 or adjust\$4) near5 (wall or chamber or reactor) near5 temperature))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:03
19	19	((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and (ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$5))) same ((control\$5 or regulat\$3 or optimiz\$5 or monitor\$3 or adjust\$4) near5 (wall or chamber or reactor) near5 temperature))) not ((ASM.as. or Lindfors.in. or Bondestam.in.) and ((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$5))) same ((control\$5 or regulat\$3 or optimiz\$5 or monitor\$3) near5 (wall or chamber or reactor) near5 temperature)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:03
20	9	((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and (ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$5))) and ((substrate near5 temperature) with (differ\$4 or increas\$3 or decreas\$3 or higher or lower or greater or lesser) with ((wall or reactor or chamber) near5 temperature)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:06

21	11	((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$5))) and (((substrate or support or pedestal or wafer) near5 temperature) with (differ\$4 or increas\$3 or decreas\$3 or higher or lower or greater or lesser) with ((wall or reactor or chamber) near5 temperature)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:36
22	10	((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$5))) and (((substrate or support or pedestal or wafer) near5 temperature) with (differ\$4 or increas\$3 or decreas\$3 or higher or lower or greater or lesser) with ((wall or reactor or chamber) near5 temperature))) ) not ((ASM.as. or Lindfors.in. or Bondestam.in.) and ((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$5))) and ((substrate near5 temperature) with (differ\$4 or increas\$3 or decreas\$3 or higher or lower or greater or lesser) with ((wall or reactor or chamber) near5 temperature))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:07
23	6	((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$6))) with (wall or reactor or chamber) with (reduc\$5 or minimiz\$6 or lower or low\$3 or prevent\$5 or eliminat\$6) with rate)	USPAT; US-PGPUB	2004/08/24 13:17
24	57	((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$6))) with (wall or reactor or chamber) with (reduc\$5 or minimiz\$6 or lower or low\$3 or prevent\$5 or eliminat\$6))	USPAT; US-PGPUB	2004/08/24 13:13
25	51	((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$6))) with (wall or reactor or chamber) with (reduc\$5 or minimiz\$6 or lower or low\$3 or prevent\$5 or eliminat\$6))) not (((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$6))) with (wall or reactor or chamber) with (reduc\$5 or minimiz\$6 or lower or low\$3 or prevent\$5 or eliminat\$6) with rate))	USPAT; US-PGPUB	2004/08/24 13:13

26	11	((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$6))) with (wall or reactor or chamber) with (rate near4 (ALE or ALD or deposit\$3 or grow\$4)))	USPAT; US-PGPUB	2004/08/24 13:18
27	37	((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$6))) near4 wall)	USPAT; US-PGPUB	2004/08/24 13:21
28	26	((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$6))) near4 wall) ) not (((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$6))) near4 wall))	USPAT; US-PGPUB	2004/08/24 13:21
29	36	((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$6))) same ((deposit\$3 or decompos\$5 or condens\$5 or contaminat\$4 or coat\$3 or grow\$4) near3 (minimiz\$5 or eliminat\$3 or prevent\$3 or avoid\$5 or reduc\$6 or low\$4) with (chamber or vessel or reactor or wall) with (hot or cold or temperature or heat\$3 or cool\$3)))	USPAT; US-PGPUB	2004/08/24 13:24
30	27	((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$6))) same ((deposit\$3 or decompos\$5 or condens\$5 or contaminat\$4 or coat\$3 or grow\$4) near3 (minimiz\$5 or eliminat\$3 or prevent\$3 or avoid\$5 or reduc\$6 or low\$4) with (chamber or vessel or reactor or wall) with (hot or cold or temperature or heat\$3 or cool\$3))) not (((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and (ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$6))) and ((deposit\$3 or decompos\$5 or condens\$5 or contaminat\$4 or coat\$3) near3 (minimiz\$5 or eliminat\$3 or prevent\$3 or avoid\$5) with (chamber or vessel or reactor or wall)))	USPAT; US-PGPUB	2004/08/24 13:25
31	25	((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$6))) same ((deposit\$3 or decompos\$5 or condens\$5 or contaminat\$4 or coat\$3 or grow\$4) with (wall) with (hot or cold or temperature or heat\$3 or cool\$3)))	USPAT; US-PGPUB	2004/08/24 13:28
32	10	((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$6))) same ((deposit\$3 or decompos\$5 or condens\$5 or contaminat\$4 or coat\$3 or grow\$4) with (wall) with (hot or cold or temperature or heat\$3 or cool\$3))) not ((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$6))) same ((deposit\$3 or decompos\$5 or condens\$5 or contaminat\$4 or coat\$3 or grow\$4) near3 (minimiz\$5 or eliminat\$3 or prevent\$3 or avoid\$5 or reduc\$6 or low\$4) with (chamber or vessel or reactor or wall) with (hot or cold or temperature or heat\$3 or cool\$3)))	USPAT; US-PGPUB	2004/08/24 13:28
33	11	((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$6))) and ((wall with (substrate or support or base or susceptor or wafer) with (higher or lower or different or difference or greater or lesser or increas\$4 or decreas\$4) with (temperature)))	USPAT; US-PGPUB	2004/08/24 13:31

34	0	((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$6))) and ((wall with (substrate or support or base or susceptor or wafer) with (higher or lower or different or difference) with (temperature))))	EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:32
35	14	((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$6))) with (minimiz\$5 or eliminat\$3 or prevent\$3 or avoid\$5) with (chamber or vessel or reactor or wall)))	EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:33
36	2	((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$6))) with (minimiz\$5 or eliminat\$3 or prevent\$3 or avoid\$5) with (chamber or vessel or reactor or wall) with (hot or cold or temperature or heat\$3 or cool\$3)))	EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:34
37	1	((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$6))) same ((deposit\$3 or decompos\$5 or condens\$5 or contaminat\$4 or coat\$3) with (wall) with (hot or cold or temperature or heat\$3 or cool\$3)))	EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:35
38	6	((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$6))) near4 wall)	EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:35
39	0	((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$5))) and (((substrate or support or pedestal or wafer) near5 temperature) with (differ\$4 or increas\$3 or decreas\$3 or higher or lower or greater or lesser) with ((wall or reactor or chamber) near5 temperature)))	EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:37
40	12	((ALE or ALD or (atomic adj layer adj (deposit\$3 or epitax\$5))) and (((substrate or support or pedestal or wafer) near5 temperature) with ((wall or reactor or chamber) near5 temperature)))	EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:37